

ABSTRACT

An object of the present invention is to provide a
light-permeable electrode for use in a gallium nitride-
5 based compound semiconductor light-emitting device, the
electrode having improved light permeability and contact
resistance.

The inventive electrode comprises a light-permeable
first layer which is in contact with a surface of a p-
10 contact layer in a gallium nitride-based compound
semiconductor light-emitting device and which is capable
of providing ohmic contact, and a second layer which is
in contact with a part of a surface of said p-contact
15 layer, wherein the first layer comprises a metal, or an
alloy of two or more metals, selected from a first group
consisting of Au, Pt, Pd, Ni, Co, and Rh, and the second
layer comprises an oxide of at least one metal selected
from a second group consisting of Ni, Ti, Sn, Cr, Co, Zn,
Cu, Mg, and In.